



20VRRM Schottky Barrier Diode SS32B Surface Mount VRMS 14V SMB Package

Our Product Introduction

Basic Information

- Place of Origin: Shenzhen, Guangdong, China
- Brand Name: SOCAY
- Certification: REACH,RoHS,ISO
- Model Number: SS32B
- Minimum Order Quantity: 3000PCS
- Price: Negotiable
- Delivery Time: 5-8 work days



Product Specification

- Product Name: Schottky Barrier Diode
- Product Package: DO-214AA/SMB
- Product Max. VRRM: 20V
- Max. VRMS: 14V
- Max. VDC: 20V
- Max. IF(AV): 3A
- IFSM: 80A
- TJ: -55 To +125
- Highlight: Schottky Barrier Diode SS32B,
SMB Package Schottky Barrier Diode, SS32B



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Product Description

20VRRM Schottky Barrier Diode SS32B Surface Mount VRMS 14V SMB Package

Schottky Barrier Diode DATASHEET: [SS32B~SS320B\(SMB\)_v93.1.pdf](#)

Characteristics of Schottky Barrier Diode SS32B :

Schottky Barrier Diode SS32B Plastic package has Underwriters Laboratory Flammability Classification 94V-0.
Surface mounted applications is in order to optimize board space.
Schottky Barrier Diode SS32B has low power loss, High efficiency.
Its Green molding compound as per IEC 61249 standard.
Nice high surge capacity.
SS32B Lead free in compliance with EU RoHS 2.0.

Mechanical Data of Schottky Barrier Diode SS32B:

SS32B Case: JEDEC SMB/DO-214AA molded plastic.
Terminals: Solder plated, solderable per MIL-STD-750, Method 2026.
Schottky Barrier Diode Approx. Weight: 0.0032 ounces, 0.092 grams.
Polarity: Color band denotes cathode end.
Schottky Barrier Diode Standard packaging: 12mm tape (EIA-481).

Electrical and Thermal Characteristics of Schottky Barrier Diode SS32B:

Electrical and Thermal Characteristics of Schottky Barrier Diode SS32B												
Parameter	Sym bol	SS3 2B	SS3 3B	SS34B	SS3 5B	SS3 6B	SS3 8B	SS31 0B	SS31 5B	SS32 0B	Unit	
Schottky Barrier Diode Max. VRRM	VRR M	20	30	40	50	60	80	100	150	200	V	
Schottky Barrier Diode Max. RMS Voltage	VRM S	14	21	28	35	42	56	70	105	140	V	
Maximum VDC	VDC	20	30	40	50	60	80	100	150	200	V	
Schottky Barrier Diode Max. Average Forward Current	IF(A V)	3									A	
Peak Forward Surge Current : 8.3ms Single Half Sinewave Superimposed on Rated Load	IFS M	80									A	
Max. VF at 3A (Note 1)	VF	0.5			0.74		0.8		0.9		V	
Maximum DC Reverse Current at Rated DC Blocking Voltage	TJ=25 IR	0.2			0.05							m A
	TJ=10 0		20					10				
Schottky Barrier Diode Typical Thermal Resistance	(Note 2) RθJ A	135									/ W	
	(Note 3) RθJL	23										
Operating Junction and Storage Temperature Range	TJ, TST G	-55 to +125		-55 to +150		-65 to +175						

Notes:1.Pulse Test with PW=300μsec, 2% Duty Cycle.

2.Mounted on a FR4 PCB, single-sided copper, mini pad.

3.Mounted on a FR4 PCB, single-sided copper, with 100cm² copper pad area.

Rating and Characteristic Curves of Schottky Barrier Diode SS32B:

Fig1. Typical Forward Characteristics:

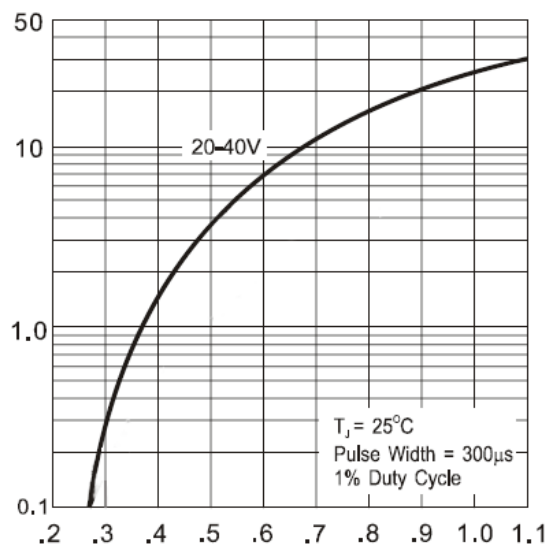
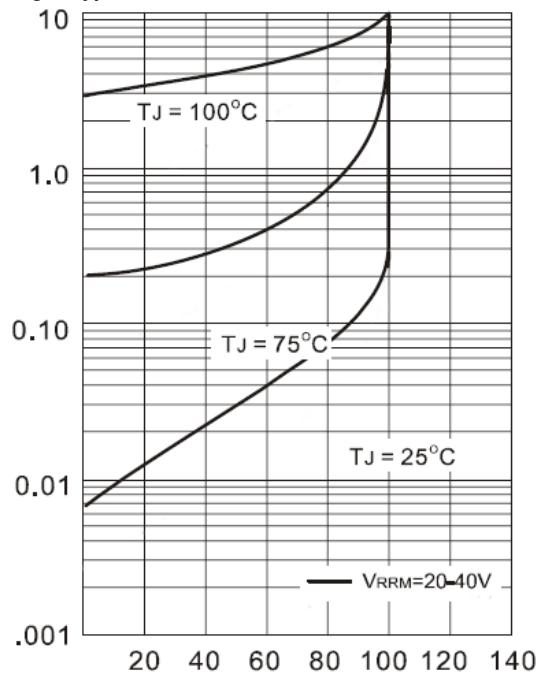
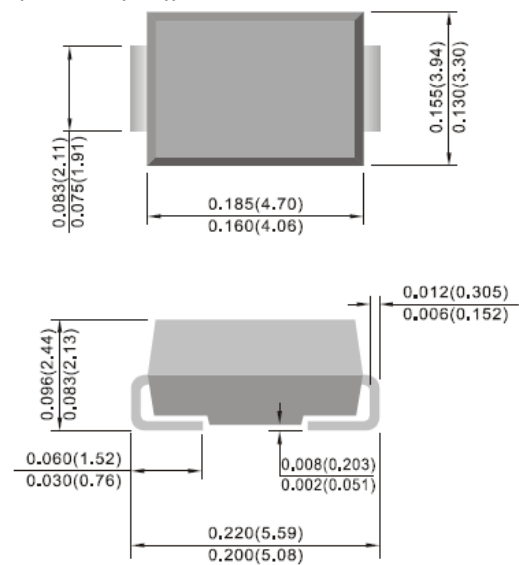


Fig2. Typical Reverse Characteristics:



DO-214AA Package Dimensions of Schottky Barrier Diode SS32B:
(Unit:inch(mm))



Packaging Information:

Part Number	Component Package	Quantity	Packaging Option
SS32B~SS320B	SMB/DO-214AA	3000 PCS	per 13" plastic Reel
		800 PCS	per 7" plastic Reel



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